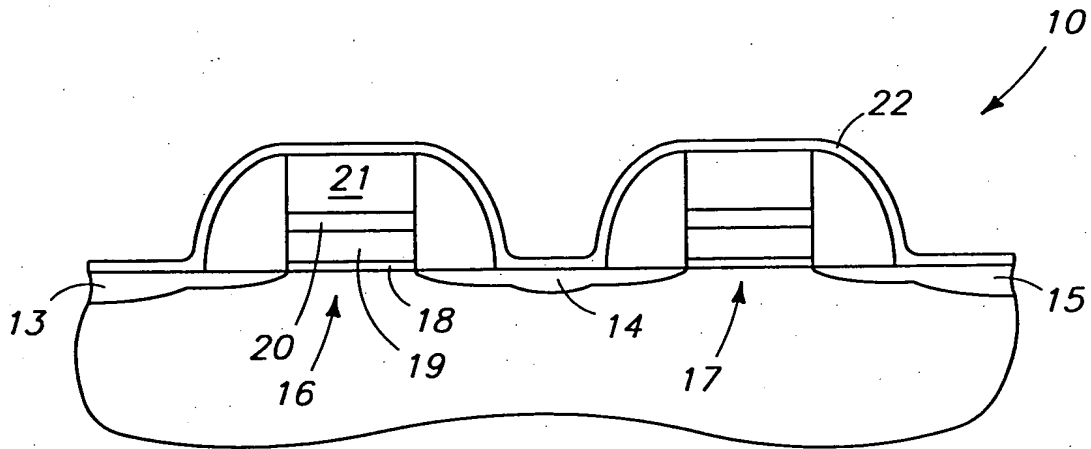
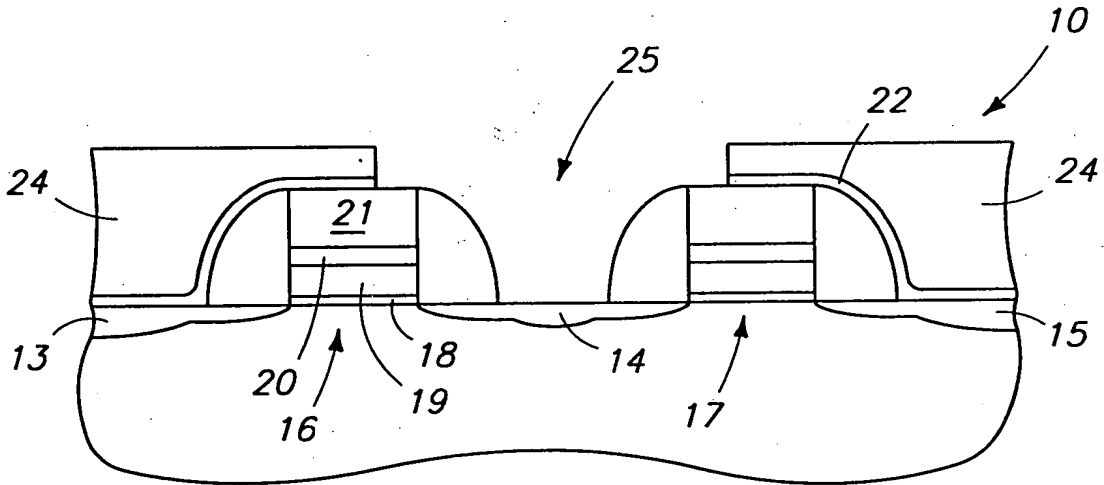


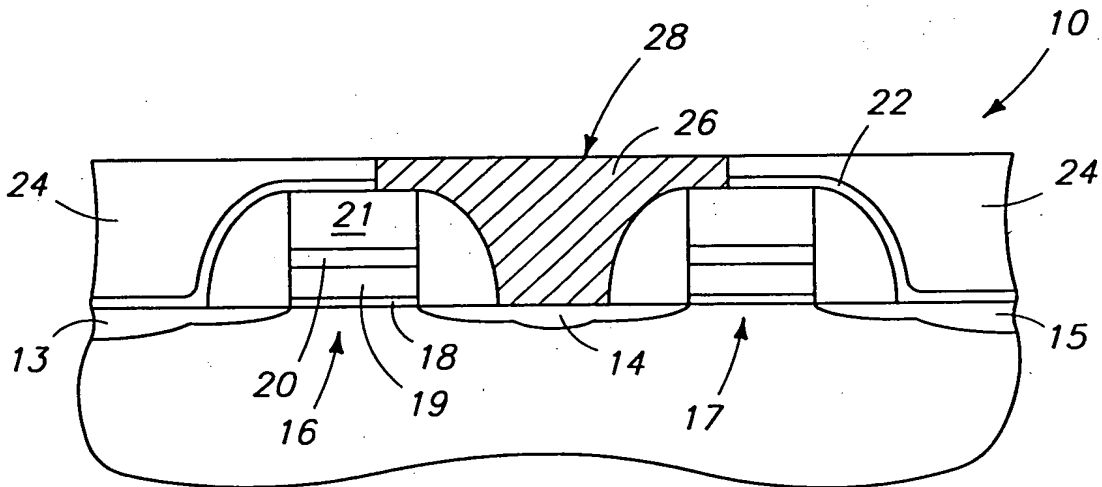
J1036 U.S. PRO  
09/876102  
06/06/01



II II II II



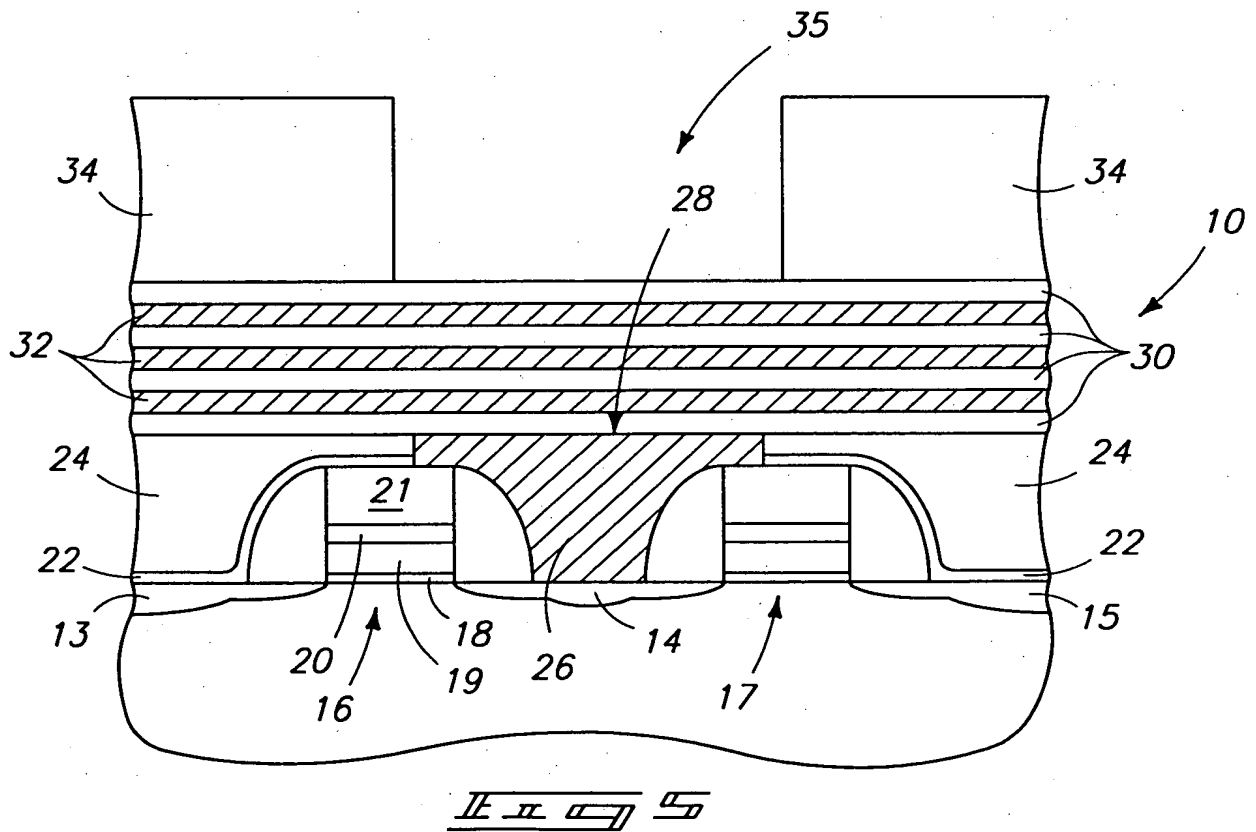
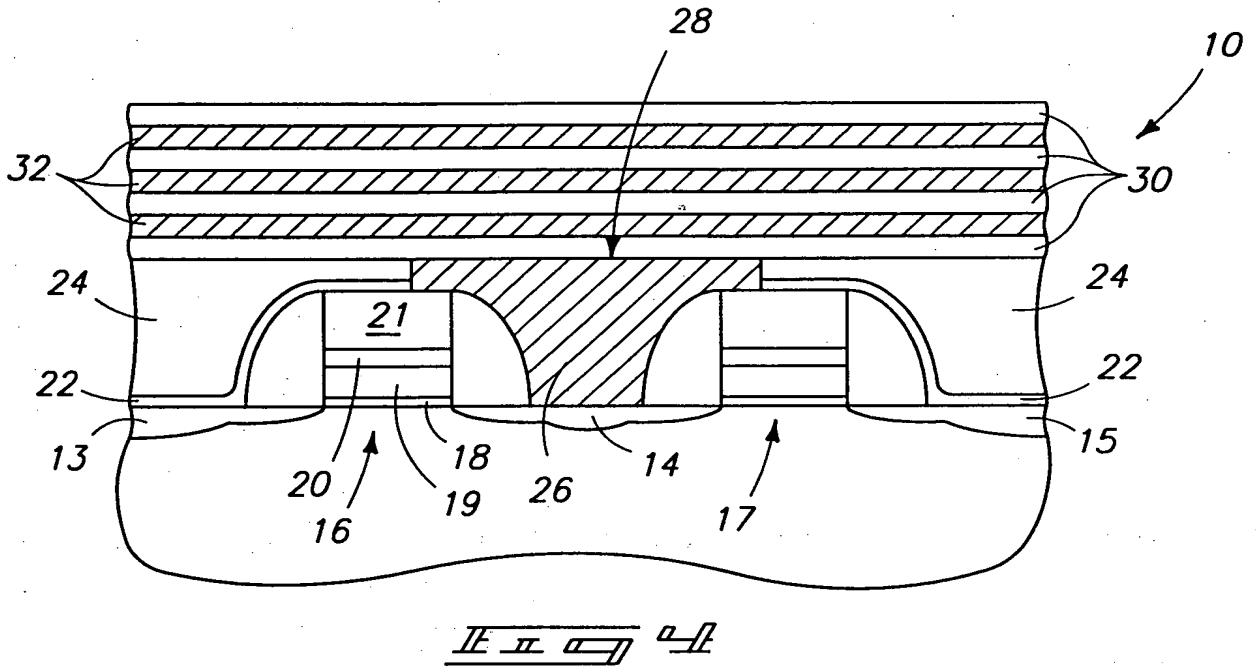
II II II II



II II II II

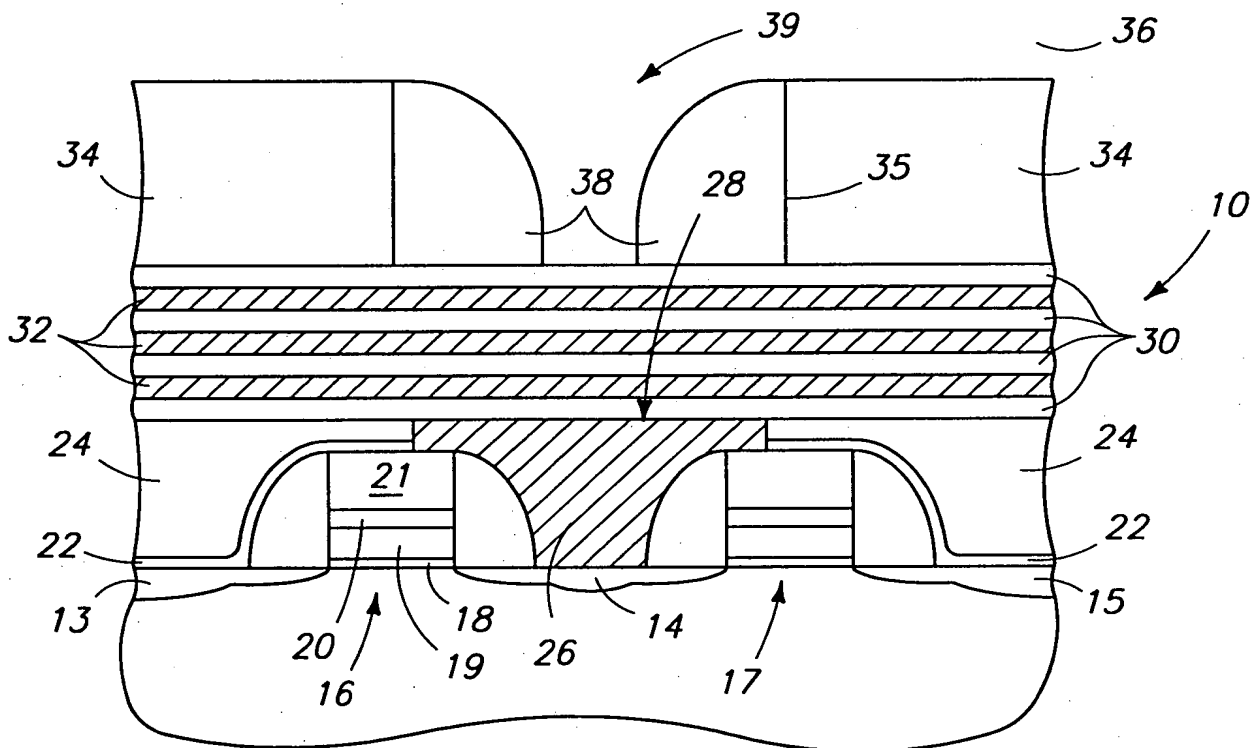
109090-20192000

AS FILED



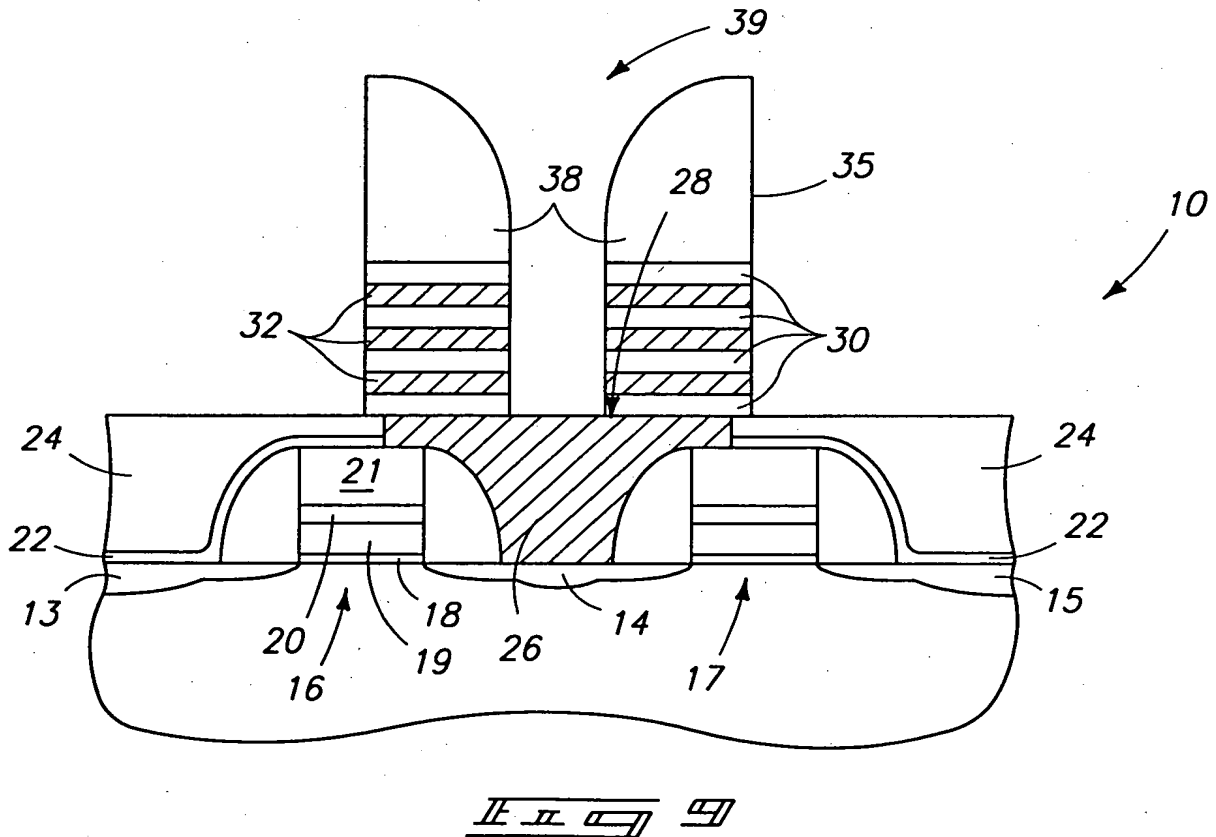
A cross-sectional view of a semiconductor device 10. The device features a substrate 13 with a base layer 15. A central region 14 is defined by a trench 16. Within this region, there is a stack of layers 17, 18, 19, and 20. A gate structure 21 is positioned over the central region 14. The device is surrounded by a dielectric material 22, which is further covered by a top layer 24. A series of horizontal layers 26, 28, and 30 are located above the central region. The device is further defined by a top layer 32, a middle layer 34, and a bottom layer 35. A final layer 36 is at the very top.

五 四 三 二 一

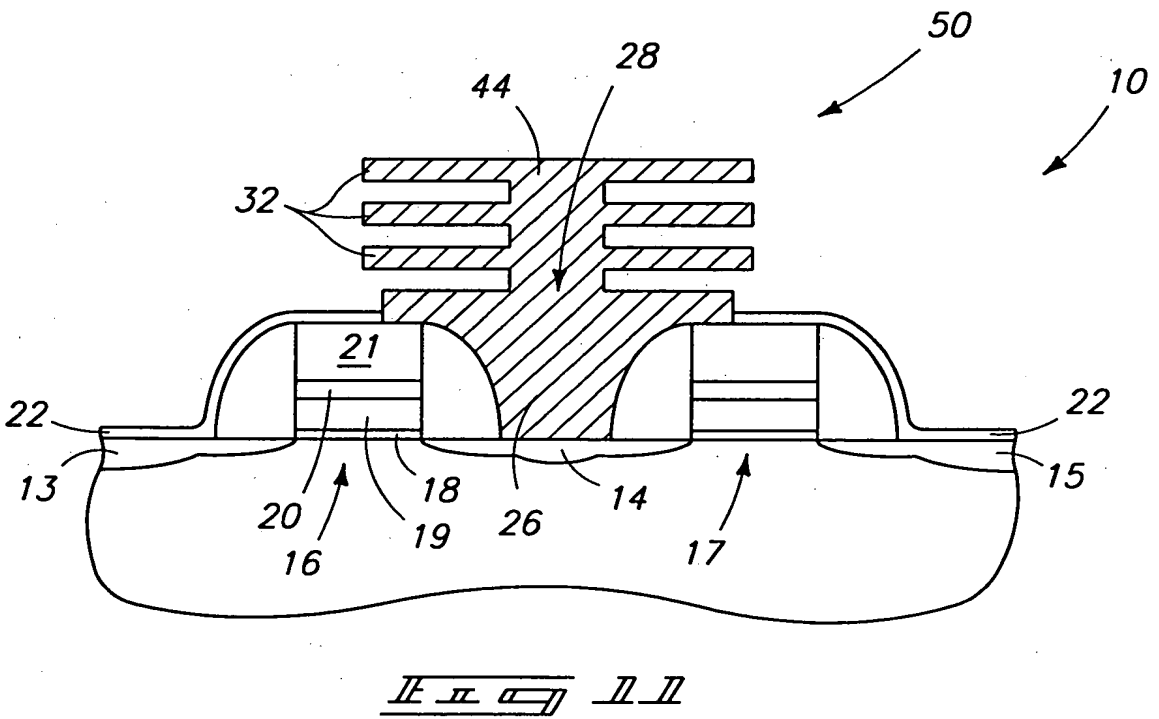
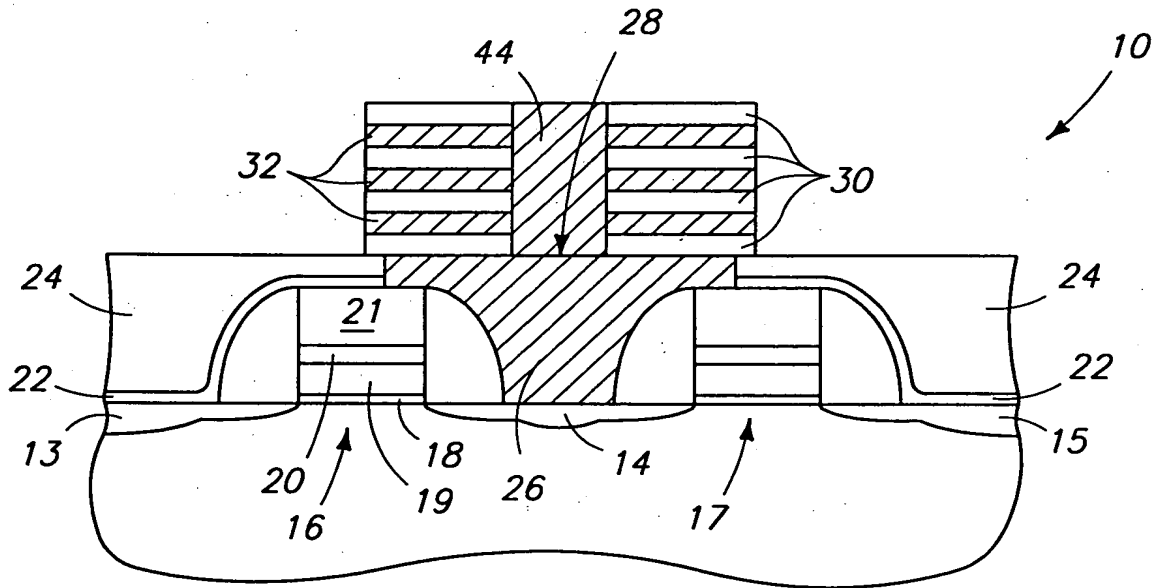


II II II II

This diagram shows a cross-sectional view of a semiconductor device 10. The device features a substrate 13 with a base layer 15. A central region 14 is filled with a material having diagonal hatching. This central region is flanked by two side regions 16 and 17, which contain horizontal hatching. Above the central region, there is a layer 20 with horizontal hatching, and a layer 21 with diagonal hatching. The device is capped with a top layer 22, which is further covered by a layer 24. A series of horizontal layers 30 are shown at the top, with a layer 32 indicated on the left. A curved structure 35 is positioned above the top layers, with a curved surface 38 and a curved surface 39.



AS FILED



09876402-060601

A cross-sectional view of a semiconductor device 10. The device features a substrate 15 with a central region 14 and side regions 16 and 17. A layer 18 is formed on the substrate, with a patterned layer 19 on top. A central block 21 is surrounded by a layer 20. A top layer 22 is formed over the central region and side regions. A central region 26 is defined by a layer 28. A top layer 32 is formed over the central region. A top layer 50 is formed over the central region. A top layer 52 is formed over the side regions. A top layer 54 is formed over the central region.

A detailed cross-sectional view of a semiconductor device 10a. The device features a substrate 13 with a base layer 15. A central region 14 is filled with a material having diagonal hatching. On either side of this central region are two identical structures, each consisting of a rectangular block 21 on a base 16, with a curved top surface 20. A layer 18 is positioned between the base 16 and the block 21, and a layer 19 is on top of the block 21. A layer 22 is located below the base 16. Above the central region 14, there is a layer 24, followed by a stack of three horizontal layers 30, each with diagonal hatching. A layer 32 is located above the stack of layers 30. A layer 35 is positioned above the layer 32. A layer 38 is located above the layer 35. A layer 39 is the topmost layer, which is curved and has a central opening. A layer 60 is located on the right side of the device, adjacent to the layer 35. A layer 26 is located between the central region 14 and the layer 24. A layer 17 is located between the base 16 and the layer 22. A layer 18 is located between the base 16 and the block 21. A layer 19 is located on top of the block 21. A layer 20 is the top surface of the block 21. A layer 21 is the rectangular block. A layer 22 is located below the base 16. A layer 24 is located above the central region 14. A layer 26 is located between the central region 14 and the layer 24. A layer 30 is a stack of three horizontal layers. A layer 32 is located above the stack of layers 30. A layer 35 is positioned above the layer 32. A layer 38 is located above the layer 35. A layer 39 is the topmost layer, which is curved and has a central opening. A layer 60 is located on the right side of the device, adjacent to the layer 35.

И И И И И И



09876105 - 060601

AS FILED

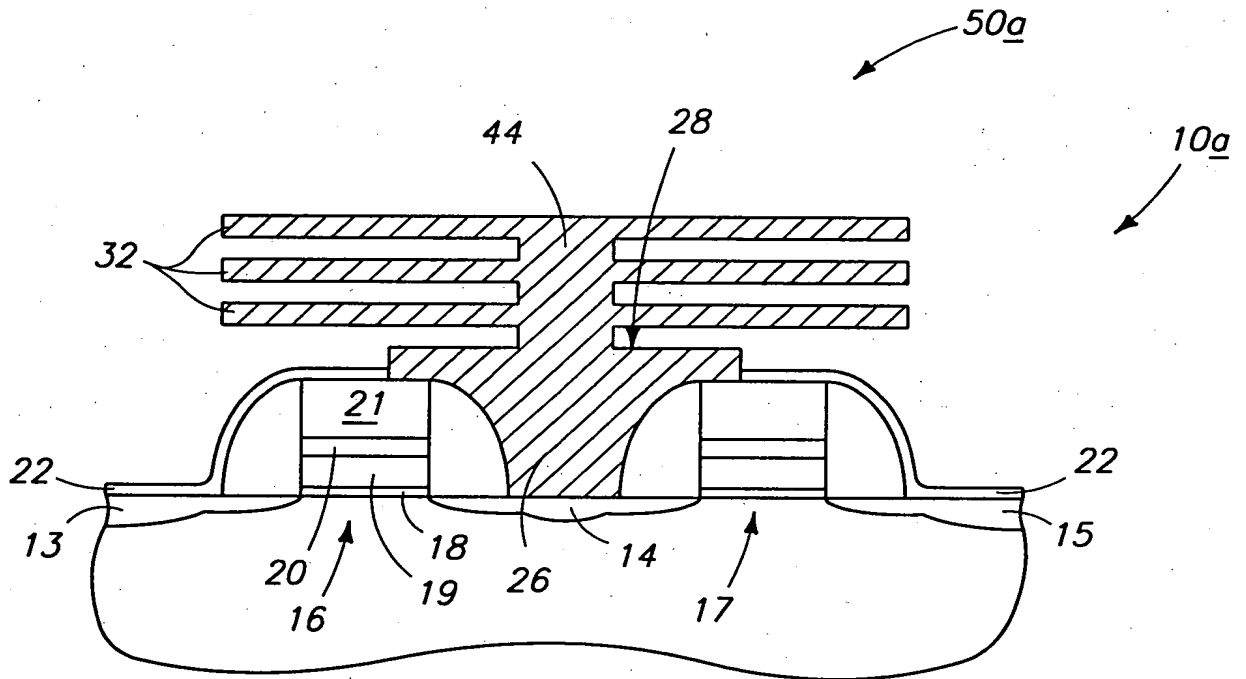
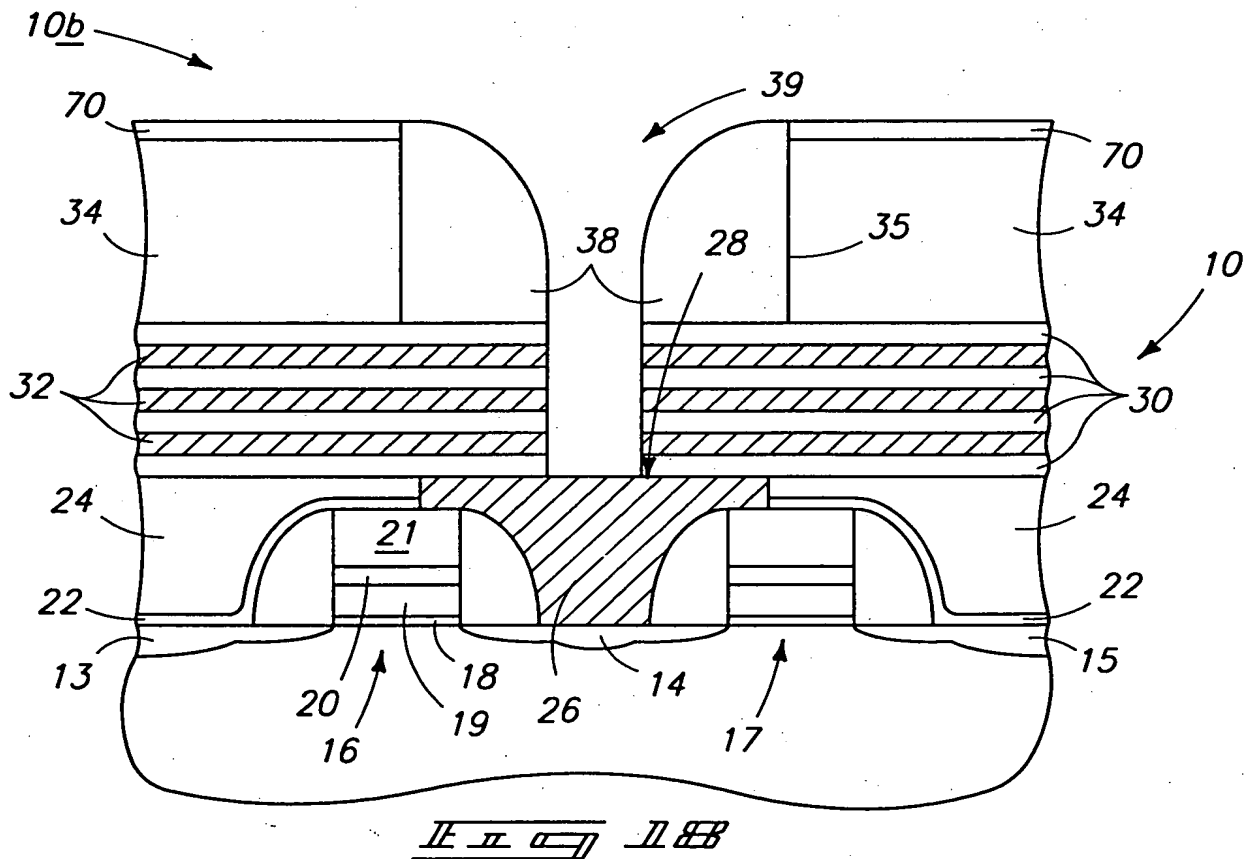
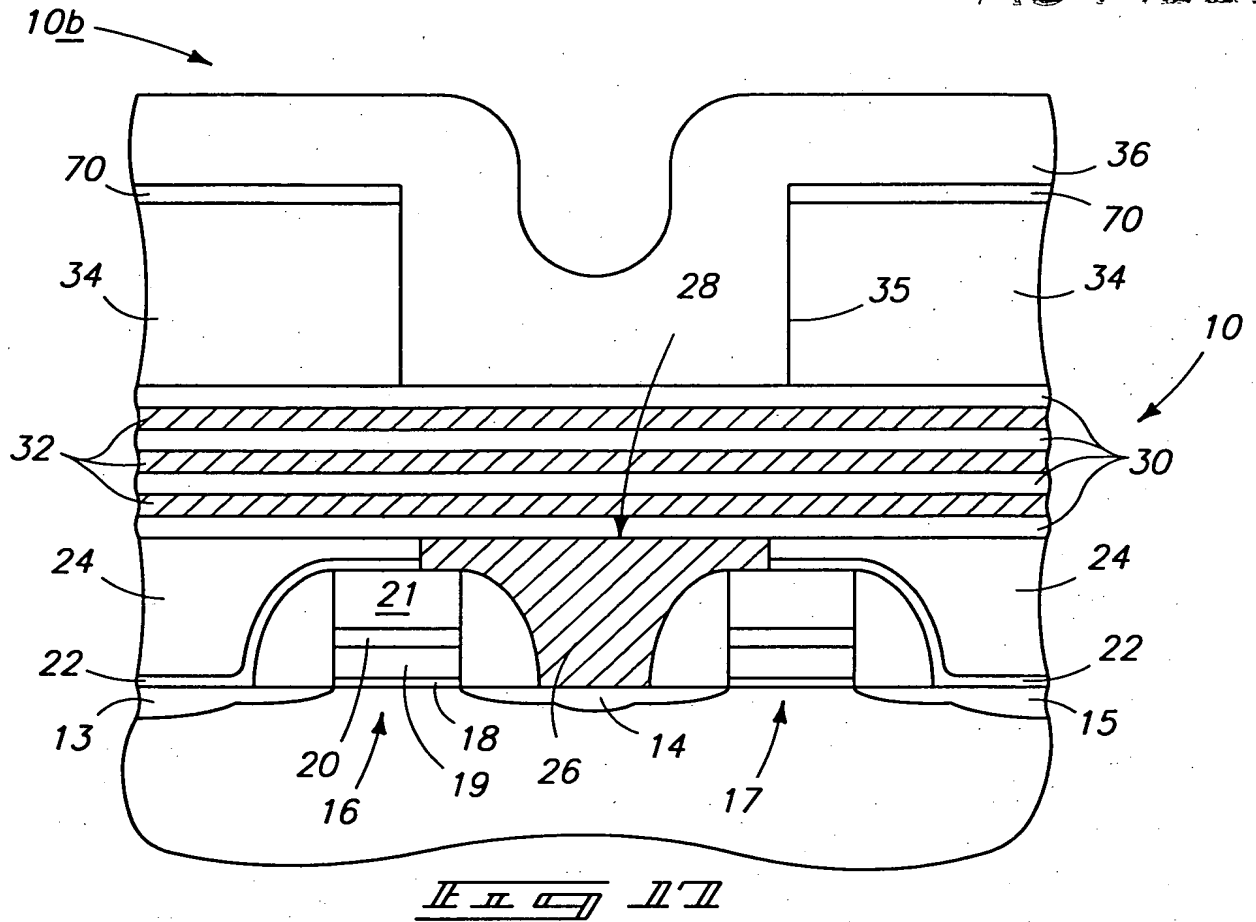


FIG. 11

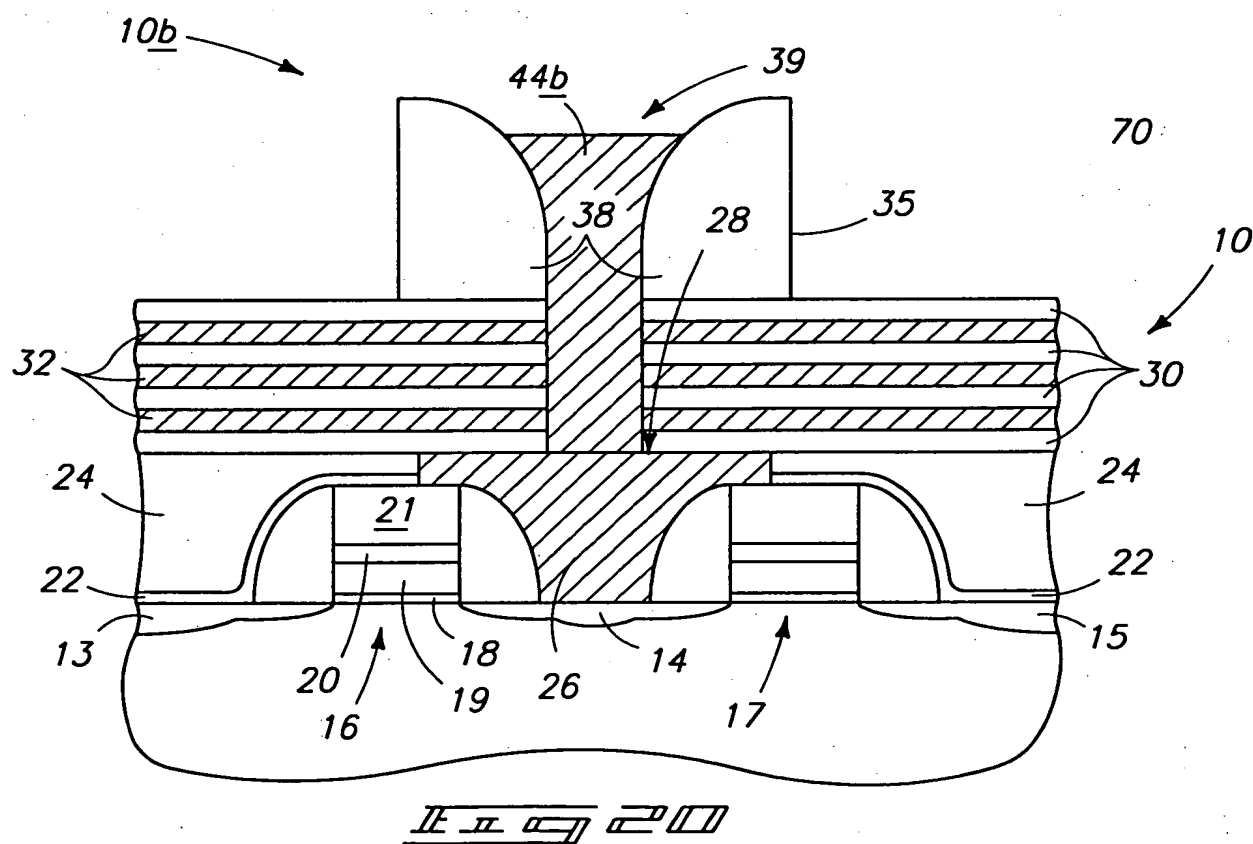
09876102.060601



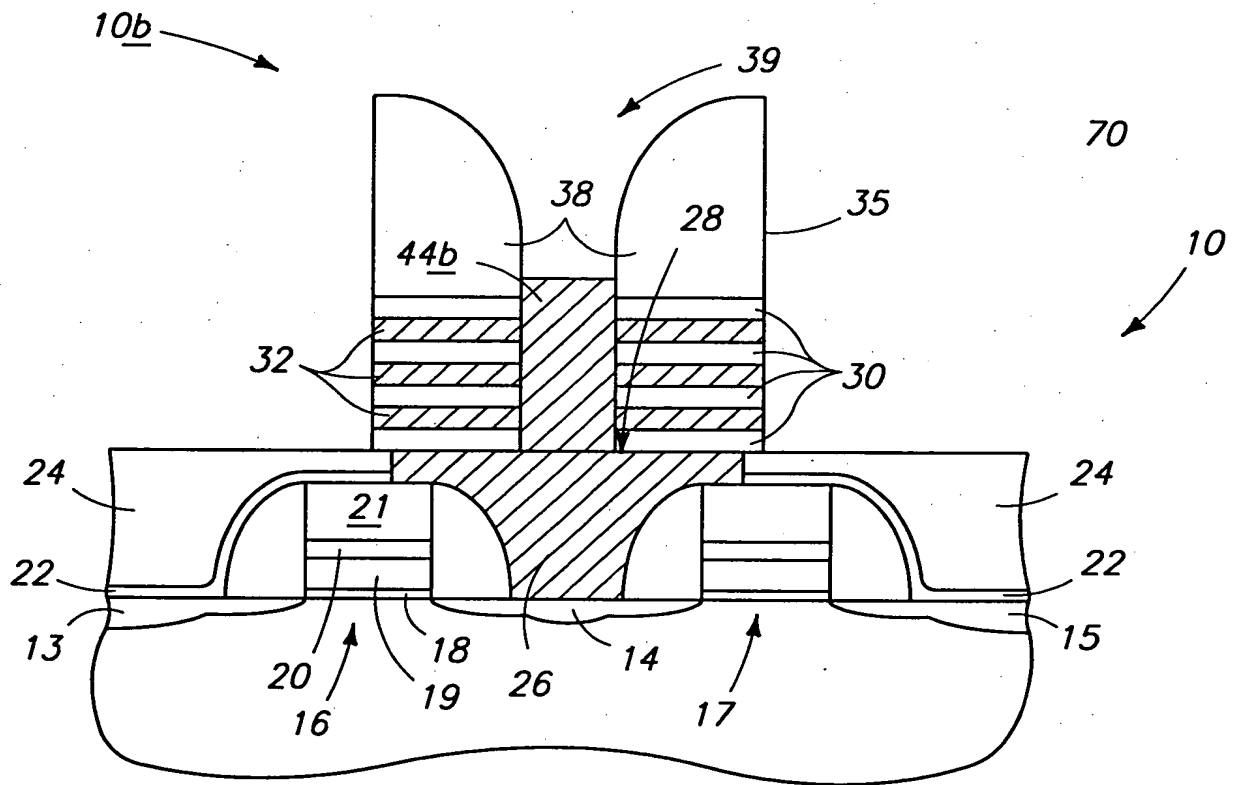
AS FILED



09876102-060601

[illegible]

AS FILED

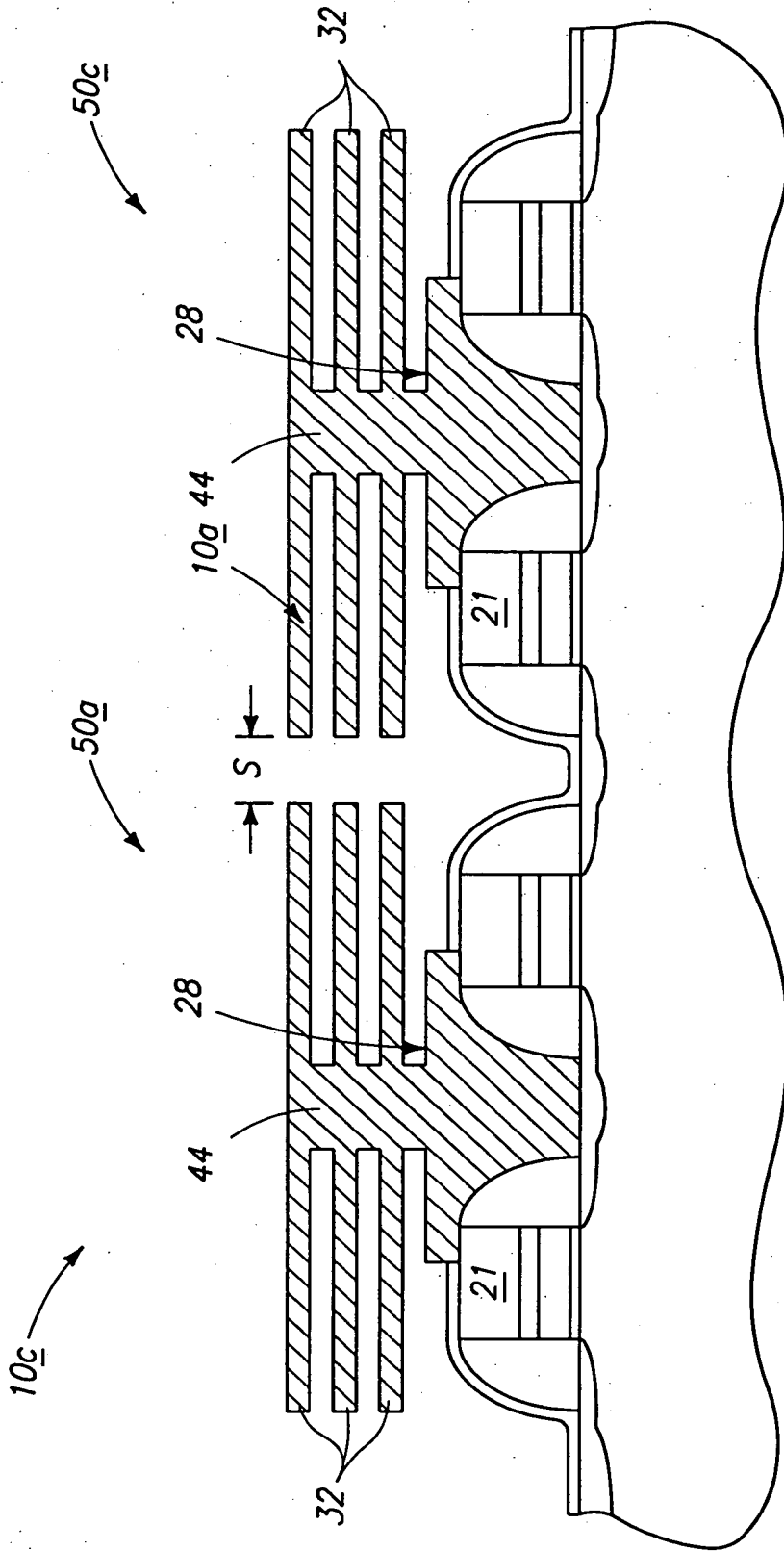


II II II II II

098102 060601

AS FILED

FO9090" 2019/2860



11 11 11 11 11